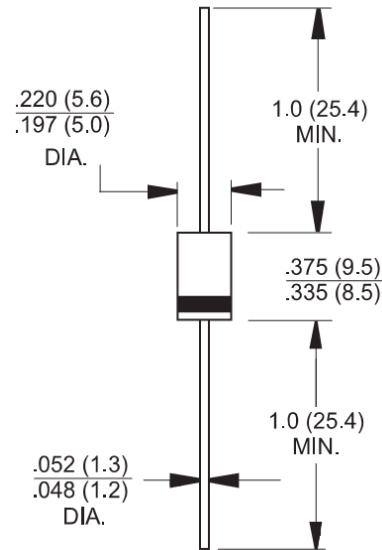


HER301G - HER308G

3.0AMPS Glass Passivated High Efficient Rectifiers

DO-201AD



Dimensions in inches and (millimeters)

Marking Diagram



HER30XG = Specific Device Code
G = Green Compound
Y = Year
WW = Work Week

Features

- ◇ Glass passivated chip junction
- ◇ High efficiency, Low VF
- ◇ High current capability
- ◇ High reliability
- ◇ High surge current capability
- ◇ For use in low voltage, high frequency inverter, free wheeling, and polarity protection application
- ◇ Green compound with suffix "G" on packing code & prefix "G" on datecode

Mechanical Data

- ◇ Case: Molded plastic
- ◇ Epoxy: UL 94V-0 rate flame retardant
- ◇ Lead: Pure tin plated, lead free, solderable per MIL-STD-202, Method 208 guaranteed
- ◇ Polarity: Color band denotes cathode
- ◇ High temperature soldering guaranteed: 260°C/10s / .375", (9.5mm) lead lengths at 5 lbs, (2.3kg) tension
- ◇ Mounting position: Any
- ◇ Weight: 1.1 grams

Maximum Ratings and Electrical Characteristics

Rating at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Type Number	Symbol	HER 301G	HER 302G	HER 303G	HER 304G	HER 305G	HER 306G	HER 307G	HER 308G	Units
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	50	100	200	300	400	600	800	1000	V
Maximum RMS Voltage	V _{RMS}	35	70	140	210	280	420	560	700	V
Maximum DC Blocking Voltage	V _{DC}	50	100	200	300	400	600	800	1000	V
Maximum Average Forward Rectified Current .375 (9.5mm) Lead Length @ T _A =55°C	I _{F(AV)}	3								A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I _{FSM}	125								A
Maximum Instantaneous Forward Voltage (Note 1) @ 3 A	V _F	1.0				1.3	1.7			V
Maximum DC Reverse Current @ T _A =25 °C at Rated DC Blocking Voltage @ T _A =125 °C	I _R	10 200								uA uA
Maximum Reverse Recovery Time (Note 2)	T _{rr}	50					75			nS
Typical Junction Capacitance (Note 3)	C _j	60					35			pF
Typical Thermal Resistance (Note 4)	R _{θJA} R _{θJL}	35 10								°C/W
Operating Temperature Range	T _J	- 65 to + 150								°C
Storage Temperature Range	T _{STG}	- 65 to + 150								°C

Note 1: Pulse Test with PW=300 usec, 1% Duty Cycle

Note 2: Reverse Recovery Test Conditions: $I_F=0.5A$, $I_R=1.0A$, $IRR=0.25A$

Note 3: Measured at 1 MHz and Applied Reverse Voltage of 4.0V D.C.

Note 4: Mount on Cu-Pad Size 16mm x 16mm on PCB

RATINGS AND CHARACTERISTIC CURVES (HER301G THRU HER308G)

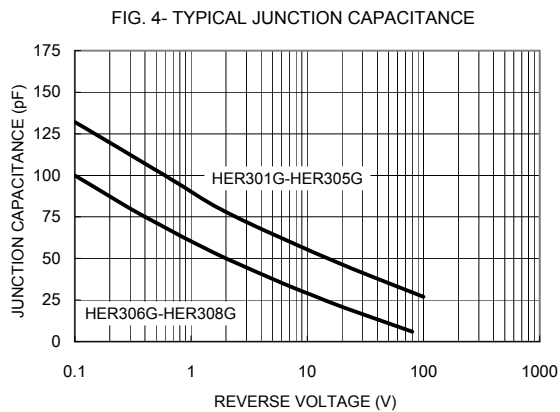
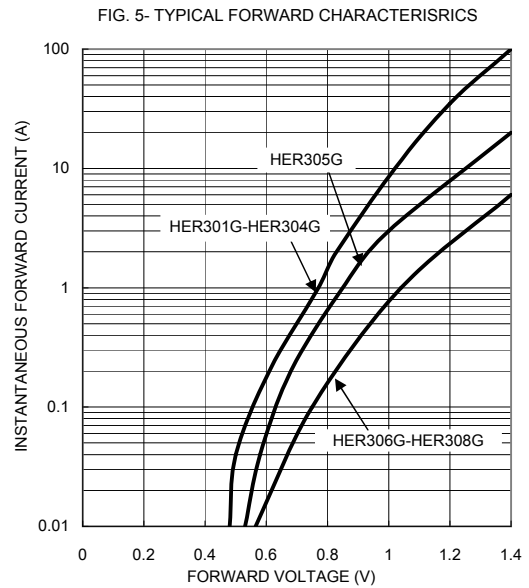
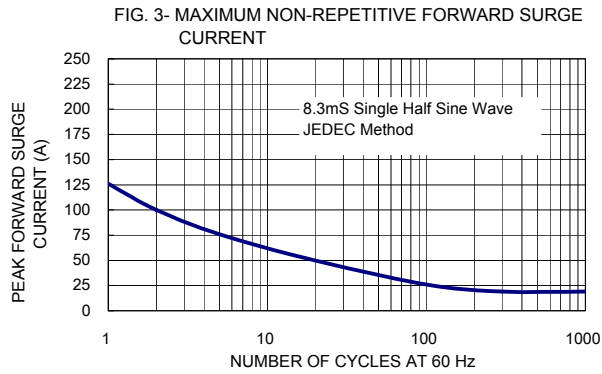
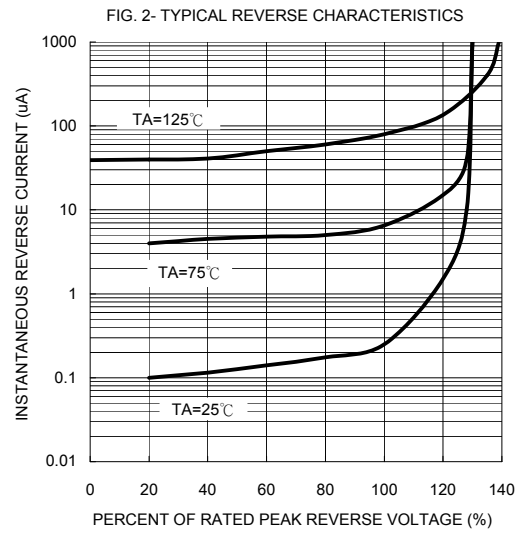
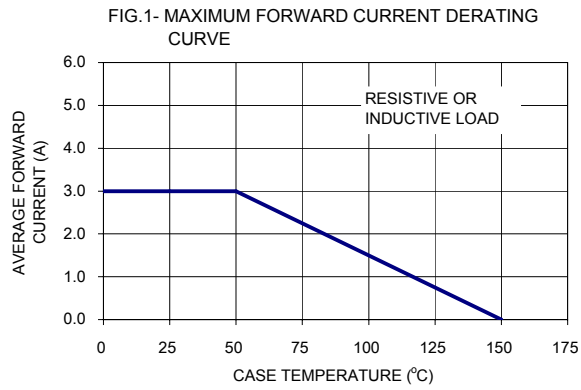


FIG.6- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM

